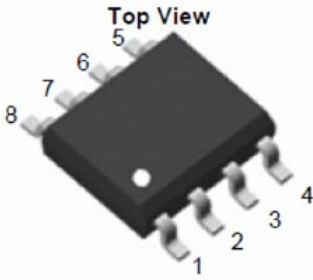
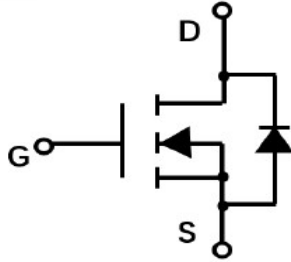
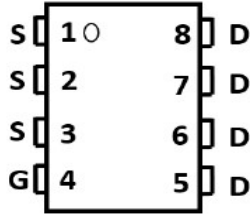


## N-Channel Enhancement Mode Field Effect Transistor



**SOP-8**



### Product Summary

- $V_{DS}$  30V
- $I_D$  18A
- $R_{DS(ON)}$  (at  $V_{GS}=10V$ ) <7.0mohm
- $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ ) <10.0mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for low  $R_{DS(ON)}$
- High Speed switching

### Applications

- Battery protection
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	30	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_A=25^\circ\text{C}$ @ Steady State	18
		$T_A=70^\circ\text{C}$ @ Steady State	14.5
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	65	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	$P_D$	3.0	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>	$R_{\theta JA}$	42	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS18N03A	F2	Q18N03.	4000	8000	64000	13" reel



# YJS18N03A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =18A		4.5	7.0	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =10A		6.6	10	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =12A, V <sub>GS</sub> =0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				18	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHZ		2191		pF
Output Capacitance	C <sub>oss</sub>			300		
Reverse Transfer Capacitance	C <sub>rss</sub>			247		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		46.3		nC
Gate-Source Charge	Q <sub>gs</sub>			8.8		
Gate-Drain Charge	Q <sub>gd</sub>			9.2		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us		1.6		
Reverse Recovery Time	t <sub>rr</sub>			11		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =15V, R <sub>L</sub> =0.75Ω R <sub>GEN</sub> =3Ω		11		ns
Turn-on Rise Time	t <sub>r</sub>			80		
Turn-off Delay Time	t <sub>D(off)</sub>			39		
Turn-off fall Time	t <sub>f</sub>			92		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R<sub>θJA</sub> is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJL</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

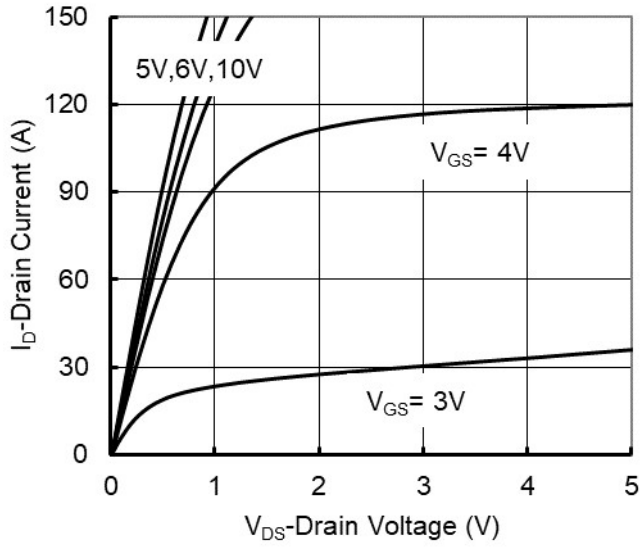


Figure 1. Output Characteristics

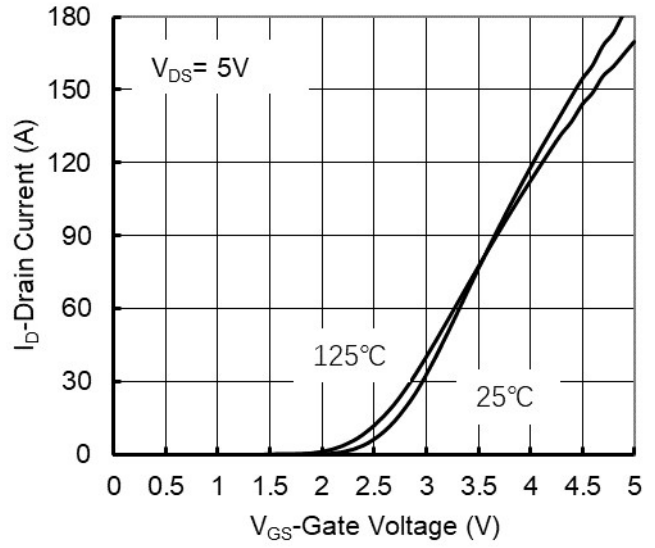


Figure 2. Transfer Characteristics

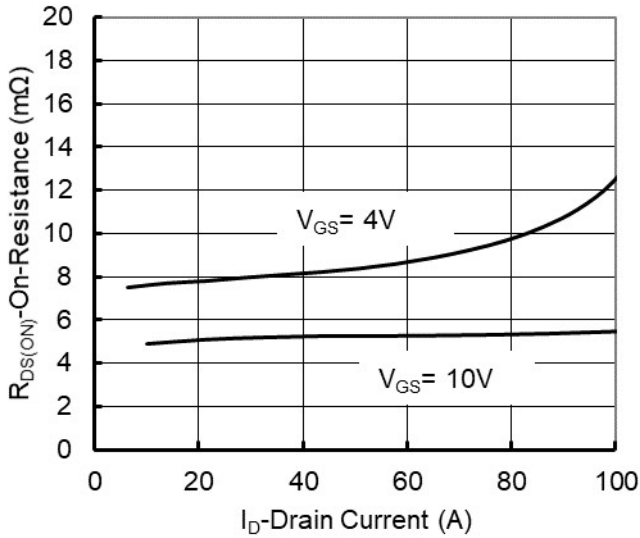


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

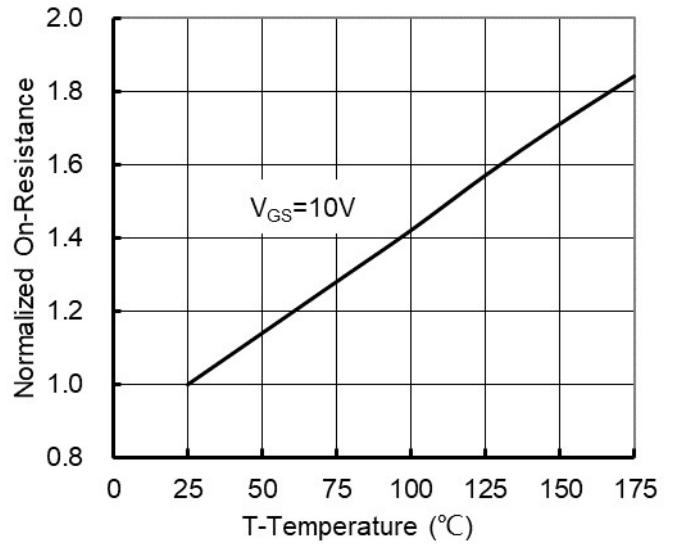


Figure 4. On-Resistance vs. Junction Temperature

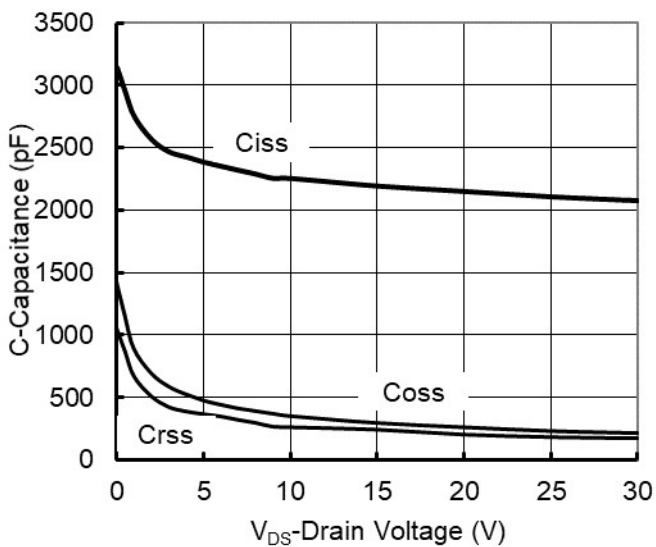


Figure 5. Capacitance Characteristics

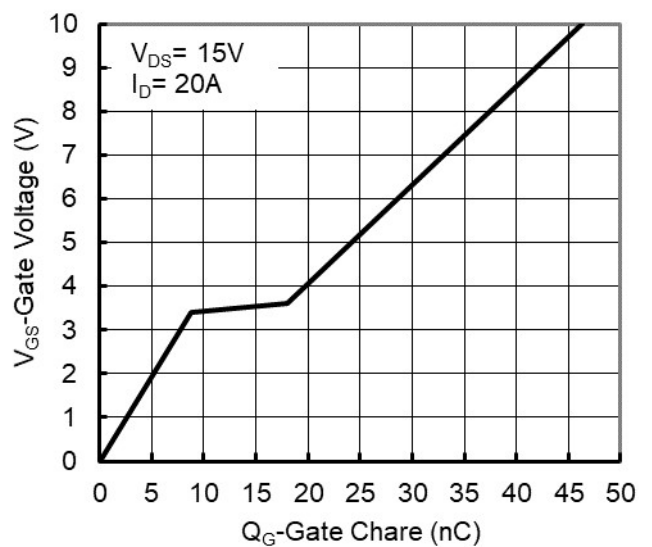


Figure 6. Gate Charge



# YJS18N03A

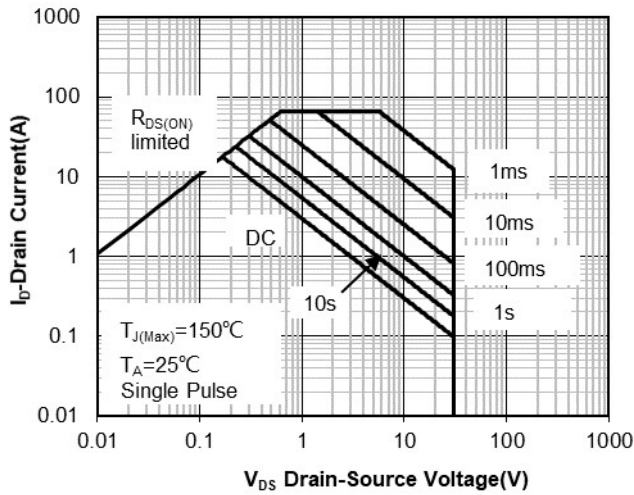


Figure 7. Safe Operation Area

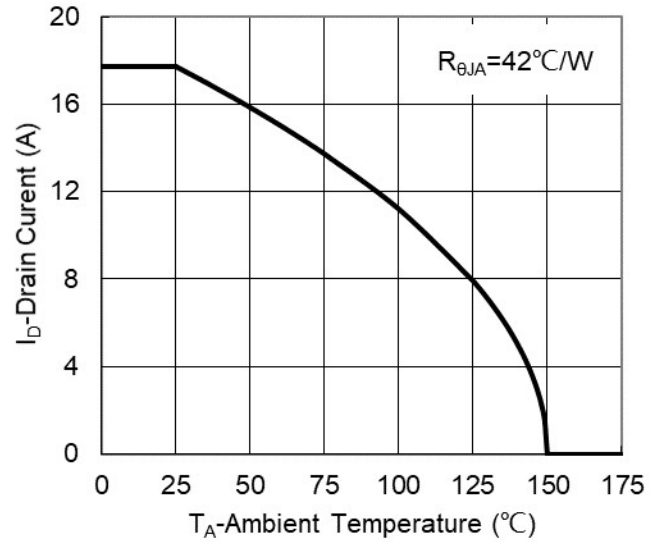


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

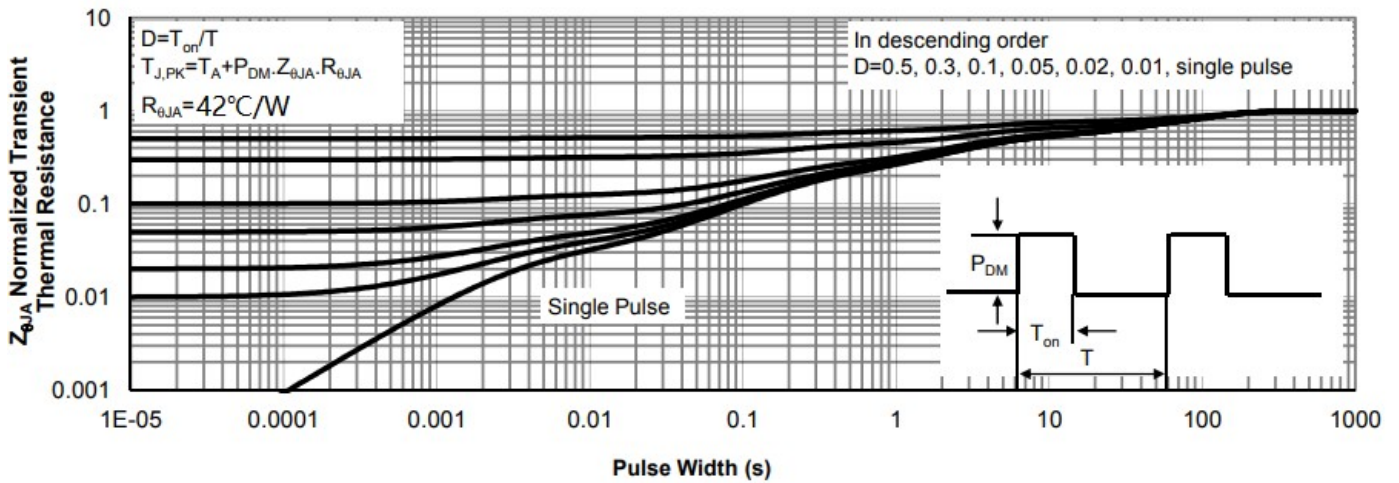
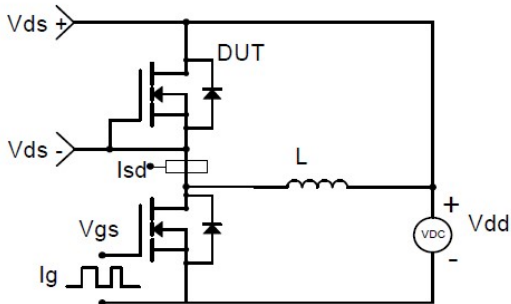


Figure 9. Normalized Maximum Transient Thermal Impedance



**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**

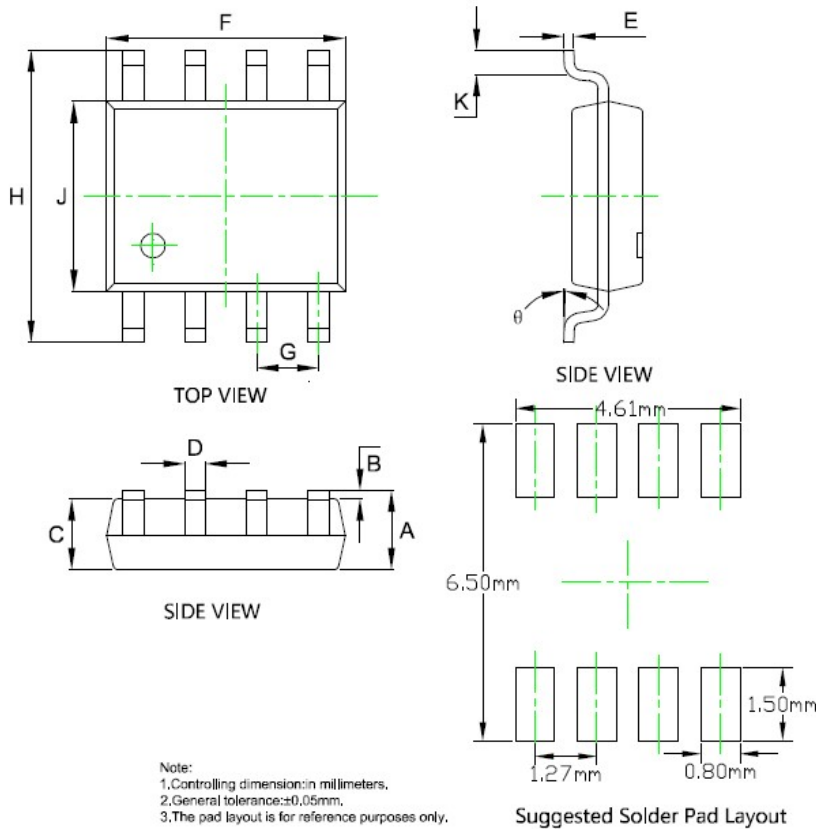


**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



# YJS18N03A

## ■ SOP-8 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
θ	0°	8°	0°	8°



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